## **DECLARATION OF JOINT INVENTORS FOR PATENT APPLICATION**

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: Plasma Enhanced Chemical Vapor Deposition Methods and Semiconductor Processing Methods of Forming Layers and Shallow Trench Isolation Regions, Serial No. 09/652,534, filed August 31, 2000.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations §1.56.

## PRIOR FOREIGN APPLICATIONS:

I hereby state that no applications for foreign patents or inventor's certificates have been filed prior to the date of execution of this declaration.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States

1	Code and that such willful false statement may jeopardize the validity of the
2	application or any patent issued therefrom.
3	* * * * * * *
4	Full name of inventor: Sujit Sharan
5	Inventor's Signature:
6	Date: $\sqrt{90}$
7	Residence: Boise, Idaho
8	Citizenship: India
9	Post Office Address: 6258 South Survival Place, Boise, ID 83716
10	* * * * * * * *
11	Full name of inventor: Gurtej S. Sandhu
12	Inventor's Signature:
13	Date:
14	Residence: Boise, Idaho
15	Citizenship: United Kingdom
16	Post Office Address: 2964 East Parkriver Drive, Boise, ID 83706
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9	Post Office Address:	6258 South Survival Place, Boise, ID 83716
10		* * * * * * * * *
11	Full name of inventor:	Gurtei S. Sandhu
12	Inventor's Signature:	Crunty Sing Sand
13	Date: 1/3/ bひ	
14'	Residence:	Boise, Idaho
15	Citizenship: United	d Kingdom
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